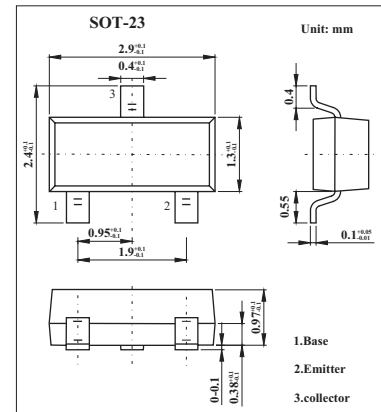


## PNP Silicon AF Transistors

### KC808(BC808)



#### ■ Features

- High collector current.
- High current gain.
- Low collector-emitter saturation voltage.

#### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-30	V
Collector-emitter voltage	$V_{CEO}$	-25	V
Emitter-base voltage	$V_{EBO}$	-5	V
Collector current (DC)	$I_C$	-800	mA
power dissipation	$P_D$	310	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65 to +150	$^\circ\text{C}$

#### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-to-baser breakdown voltage	$V_{CBO}$	$I_C = -10 \mu\text{A}, V_{BE} = 0$	-30			V
Collector-to-emitter breakdown voltage	$V_{CEO}$	$I_C = -10 \text{mA}, I_B = 0$	-25			V
Emitter-to-base breakdown voltage	$V_{EBO}$	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector cutoff current	$I_{CES}$	$V_{CB} = -25 \text{V}, V_{BE} = 0$			-100	nA
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -4 \text{V}, I_C = 0$			-100	nA
DC current gain *	$h_{FE}$	$I_C = -100 \text{mA}, V_{CE} = -1 \text{V}$	100		630	
		$I_C = -300 \text{mA}, V_{CE} = -1 \text{V}$	60			
Collector saturation voltage *	$V_{CE(sat)}$	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$			-0.7	V
Base emitter on voltage	$V_{BE(on)}$	$V_{CE} = -1 \text{V}, I_C = 300 \text{mA}$			-1.2	V
Output Capacitance	$C_{ob}$	$V_{CB} = -10 \text{V}, f = 1 \text{MHz}$			12	pF
Transition frequency	$f_T$	$I_C = -10 \text{mA}, V_{CE} = -5 \text{V}, f = 50 \text{MHz}$		100		MHz

\* Pulsed:  $PW \leq 350 \mu\text{s}$ , duty cycle  $\leq 2\%$

#### ■ Marking

NO.	KC808-16	KC808-25	KC808-40
Marking	9GA	9GB	9GC
$h_{FE}$	100 ~ 250	160 ~ 400	250 ~ 630